

Impact des radiations sur les composants et systèmes électroniques pour l'espace: **de la prédition à l'analyse**

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- Décrire la démarche assurance radiation spatiale dans un cadre plus global (lien entre analyse , tests et exploitation des essais, composants et matériaux)
- Illustrer la démarche en identifiant quelques outils et mots-clés
- Mentionner les sujets « émergents »

Space environment is a harsh medium for technologies

- Radiation

- Alpha particles & Protons
- Electrons
- Photons

- UV

- Temperature

- Thermal Cycling under Vacuum

- Atomic Oxygen

- Erosion of surfaces

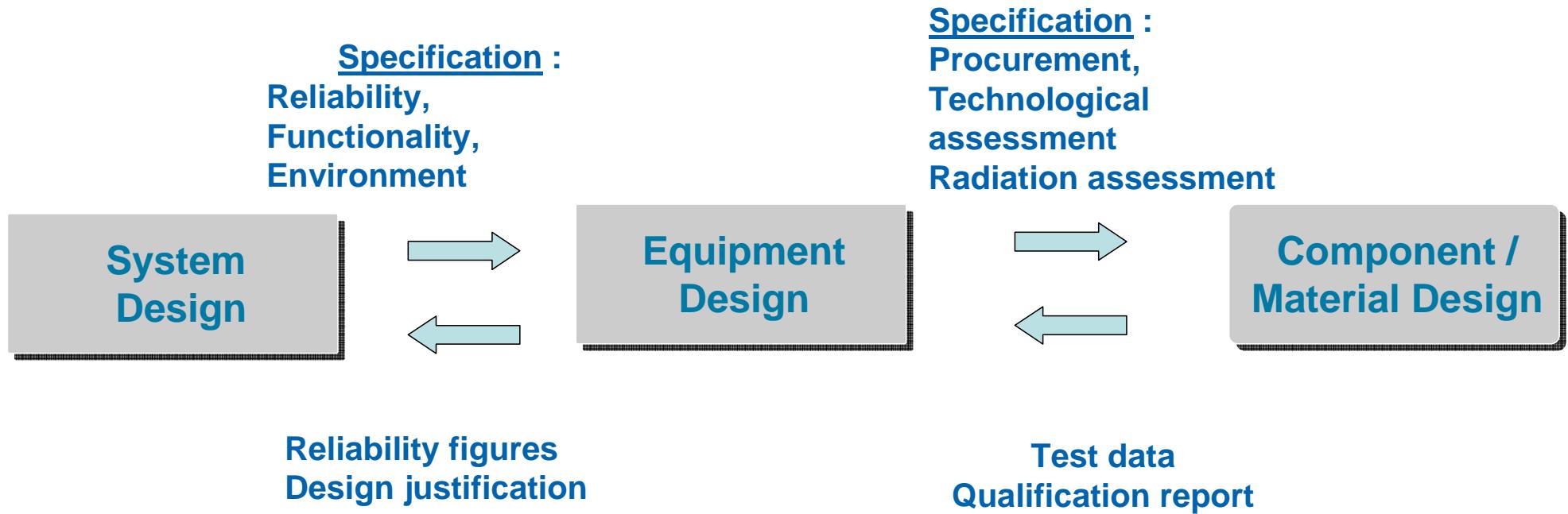
- Debris

- Impacts
- Mechanical damage



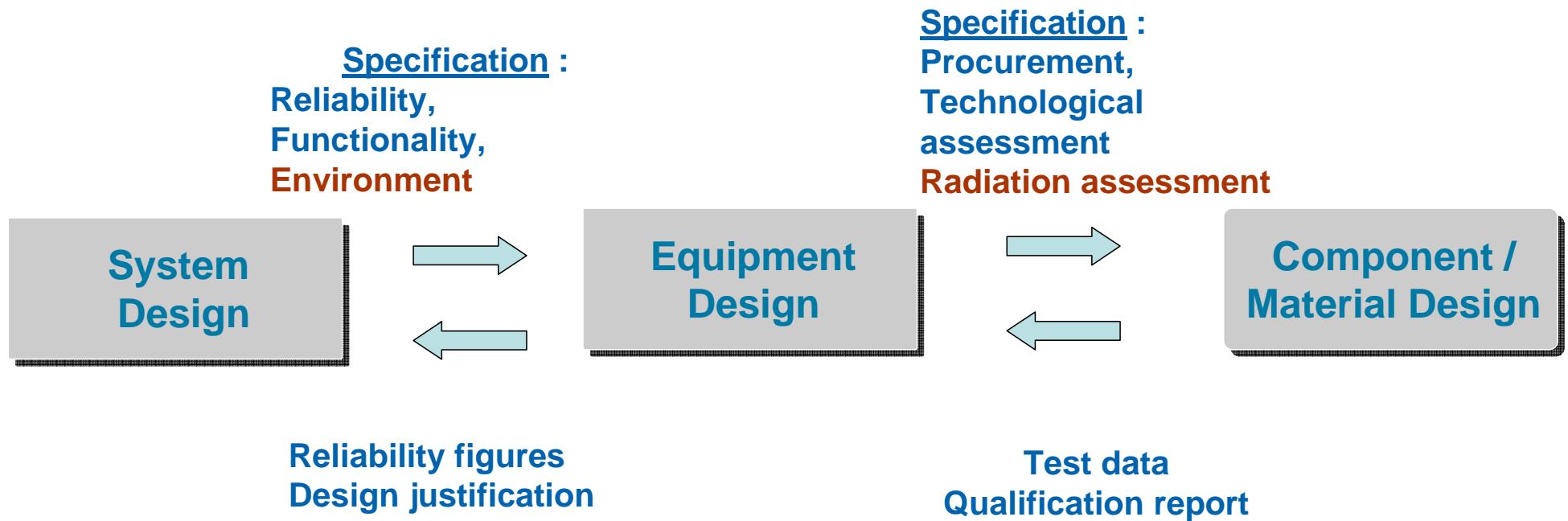
Need to ensure reliability at an acceptable cost

Radiation Assurance Process*...



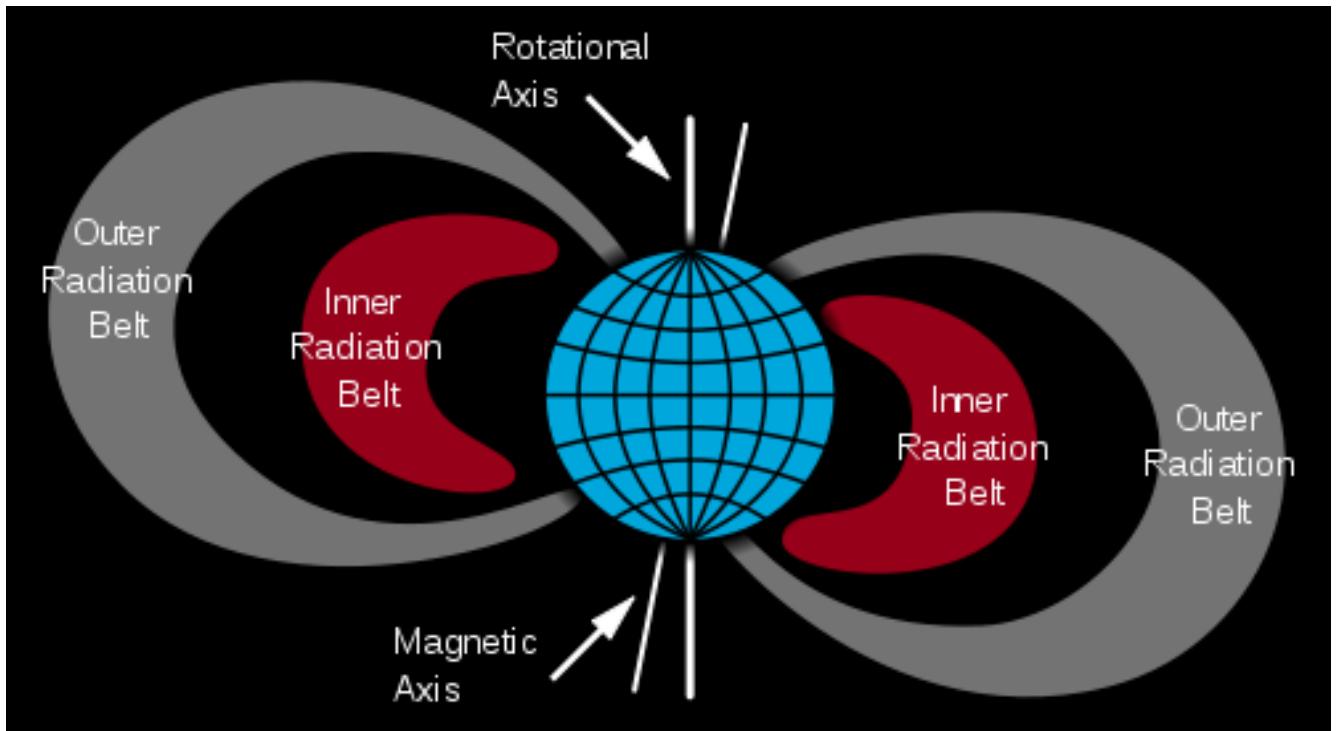
...Aims at ensuring the ability of technologies (Components, Materials) to comply to radiation requirements

- STEP 1 : Define Radiation Environment



Calculation of Space Environment

- Depends on the mission: LEO, GEO*, Interplanetary, Near Sun,...
 - Trapped Particles / Solar particles / Cosmic ray (ECSS-E-ST-10-04)



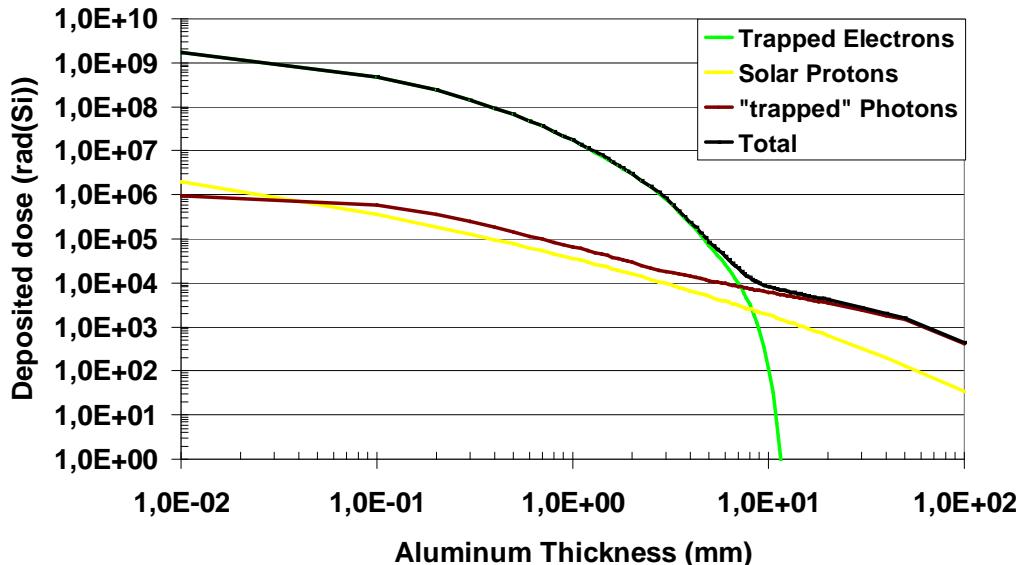
*Generally
Industrial specifications

PARTICLE FLUX Calculation tools :

OMERE (TRAD with CNES support : more than 500 users in the world)

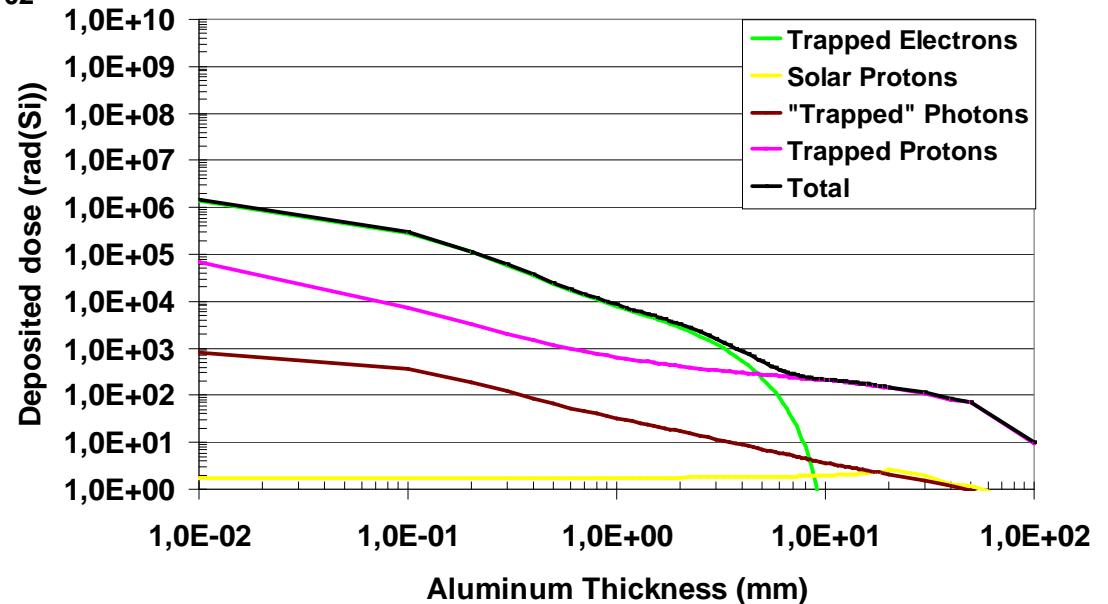
Calculation of Space Environment

DOSE-DEPTH CURVE : e.g OMERE OUTPUT



15 Years GEO

5 Years LEO ISS

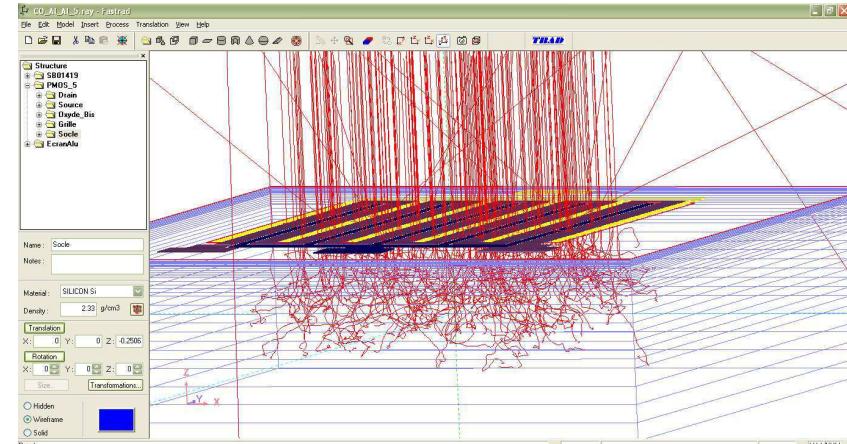
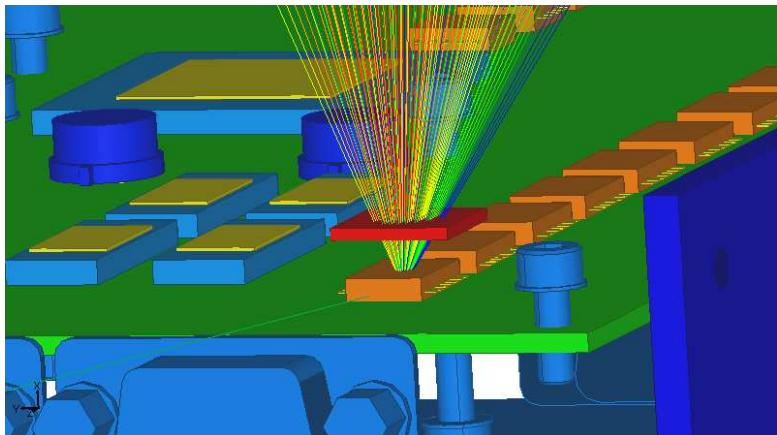


- Components

- Ray-tracing for quick calculation
- Reverse Monte Carlo for critical cases

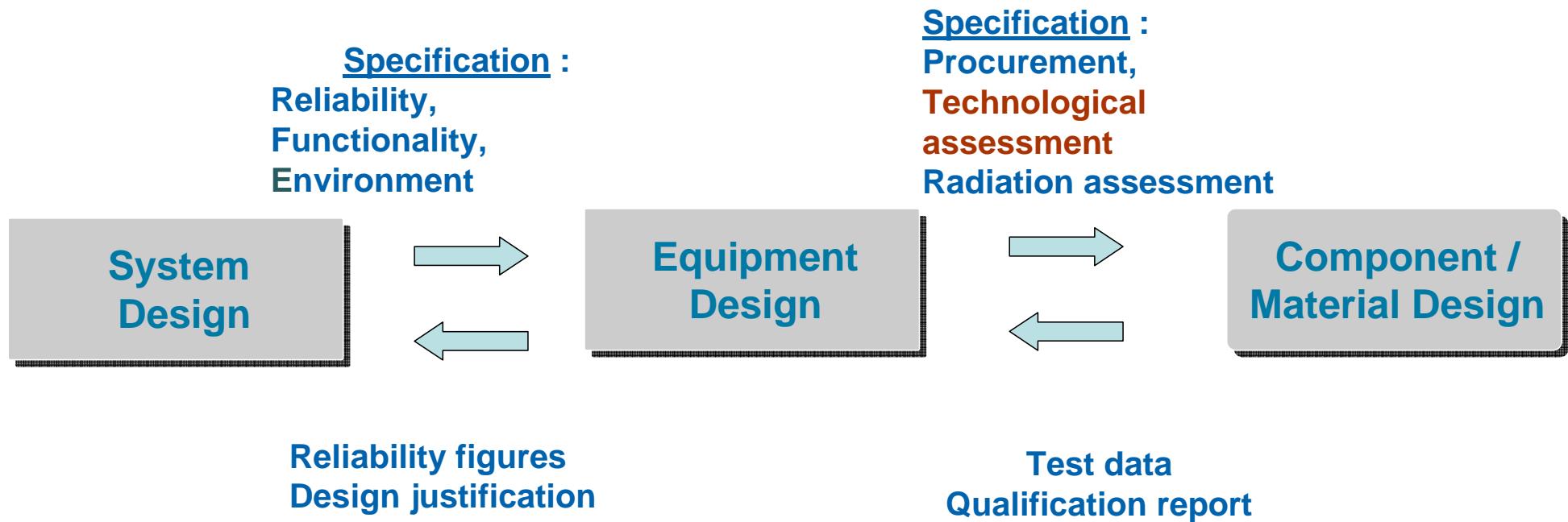
- Materials

- Direct Monte Carlo
- RayTracing only for “internal” materials



- FASTRAD TRAD's tool has become a standard in Europe (Thales, Astrium, ESA,...) but it is also used by NASA JPL, MIT, JAXA

• STEP 2 : Technological Assessment



Summary of radiation effects

Total Ionizing Dose (TID)

*Potentially all components
& Materials*

Cumulative effects

Displacement damage
*Bipolar technologies
Optical Devices & Materials*

Permanent SEEs

SEL
CMOS technologies
SEB
Power MOSFETs, BJT and diodes

SEGR
Power MOSFETs

Single Event Effects (SEE)

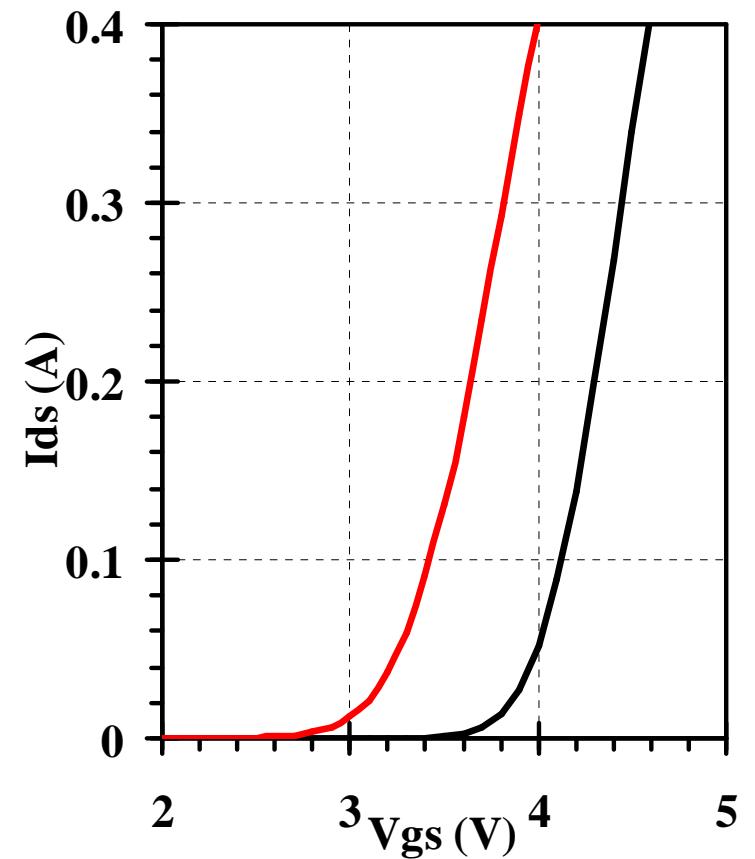
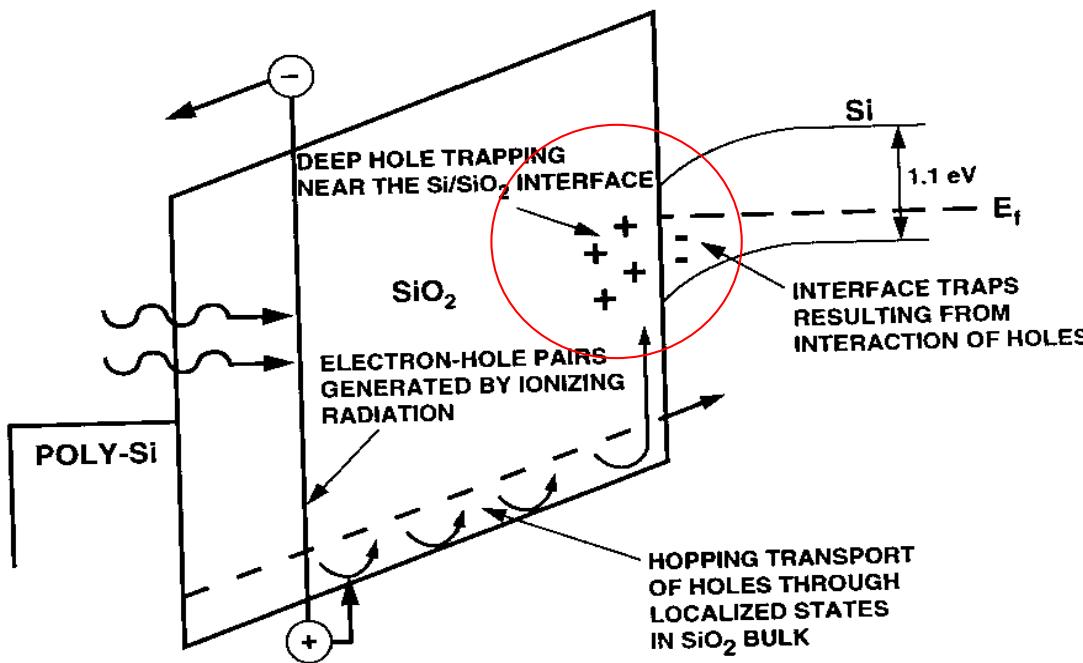
Static SEEs
SEU, SEFI
Digital ICs

Transient SEEs
*Combinational logic
Operational amplifiers*

Total Ionizing Dose

- MOS technology :

- Voltage drifts due to oxyde traps
- Std by currents -> leakage -> consumption

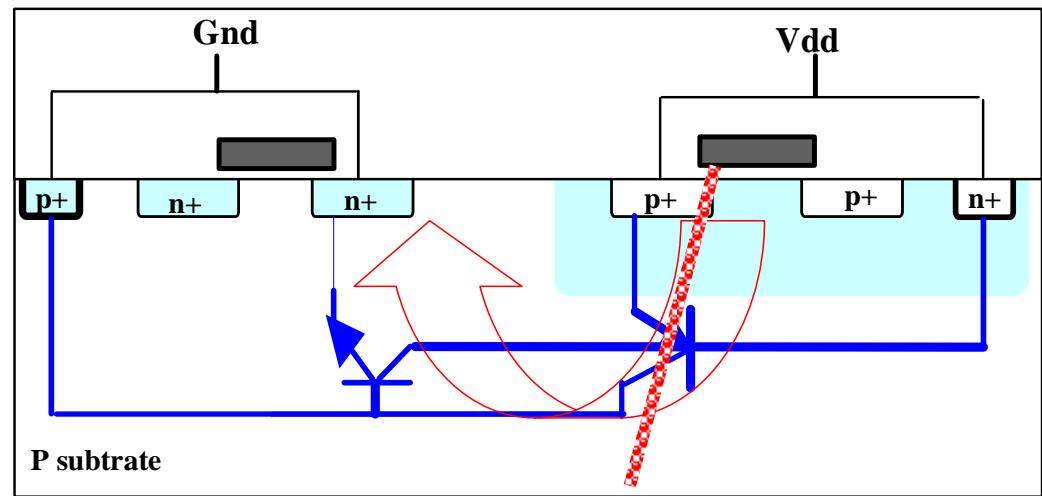
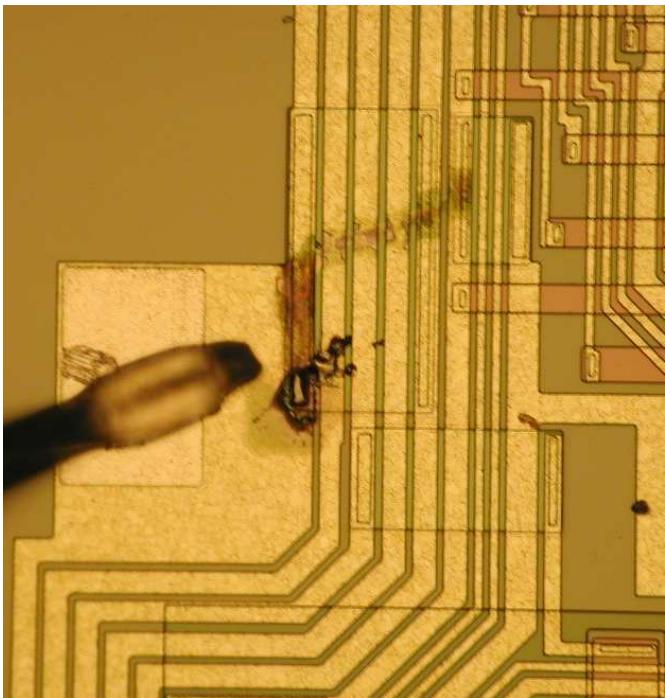


- Bipolar technologies :

- Main effect at transistor level :
 - reduction of gain $\Delta(1/\beta) = K \cdot D^N$ with $N \geq 1$ at a low level of dose.
- Bias & offset currents, increase of offset voltages
- Potential dose rate effects (low dose rate sensitivity enhancement)

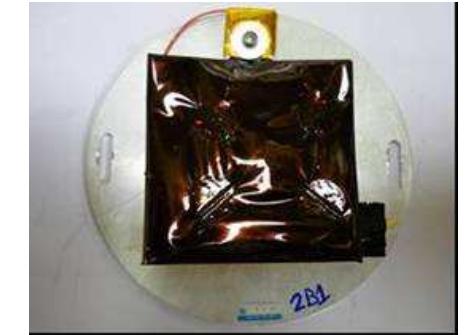
SEL Single Event Latch-up

Destructive effect (and bulk structures)

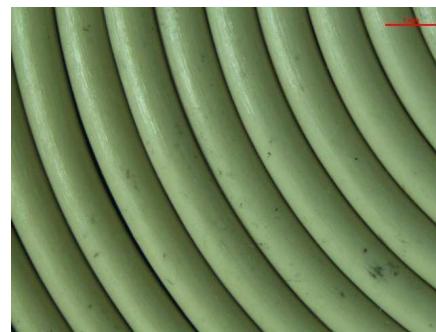
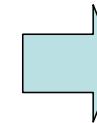


- *Potential Destruction if no delatcher*

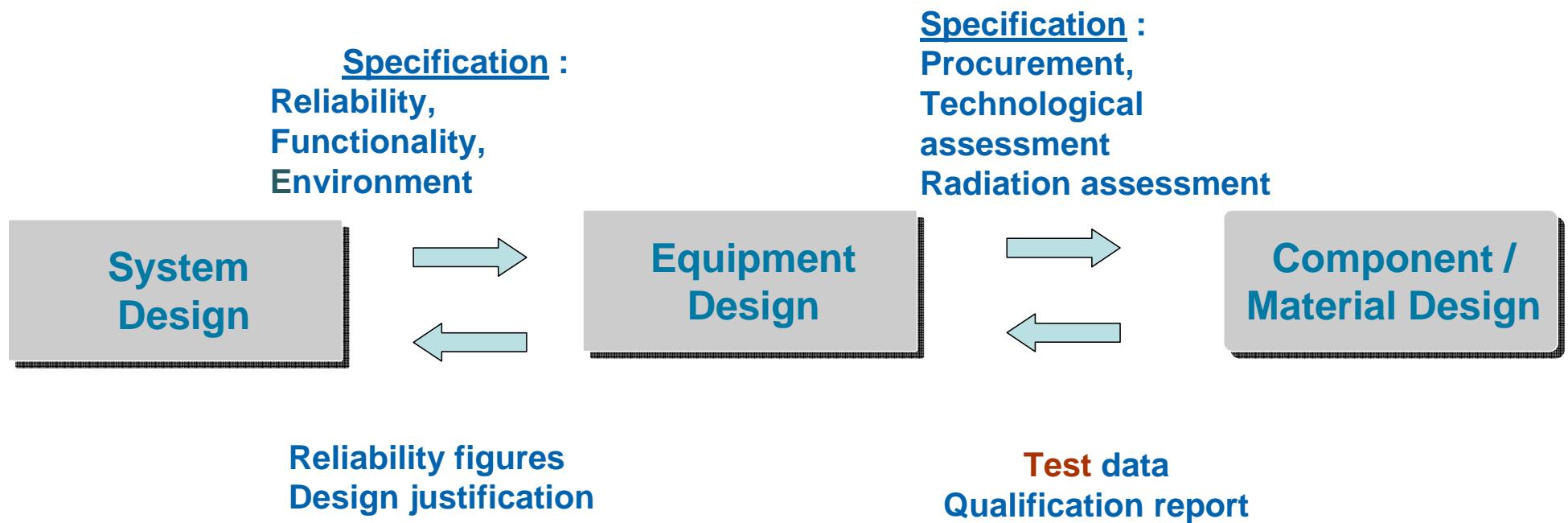
Ageing of thermal protection materials Absorptivity increase



Failure of external jacket cable material Insulation leaks



- STEP 3 : Test Definition & Realization



- **Total Ionizing Dose (ESCC 22900)**

- Dose level (dose rate x time / Co60)
- Dose rate effect

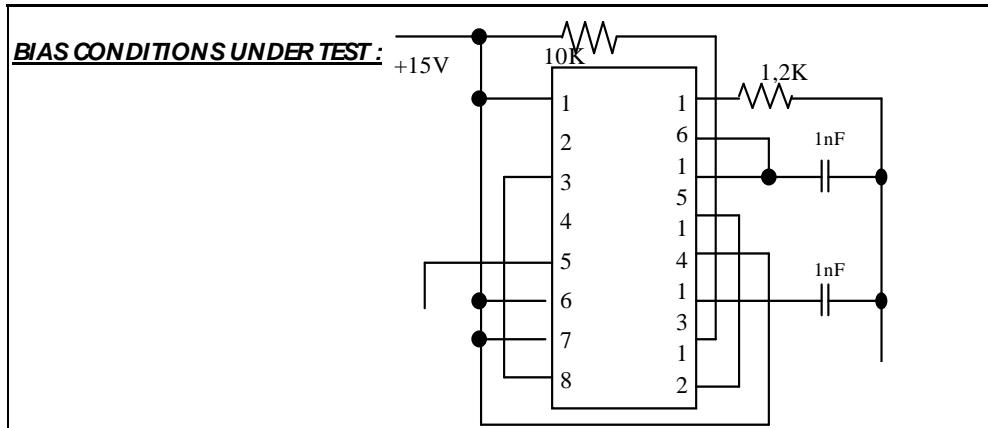
- **Single Event Effects (ESCC 25100)**

- Decapsulation / active zone (cf heavy ions penetration depth)
- Cf to pre-test, Laser

- Device configuration and Tested parameters

Irradiation Test Plan

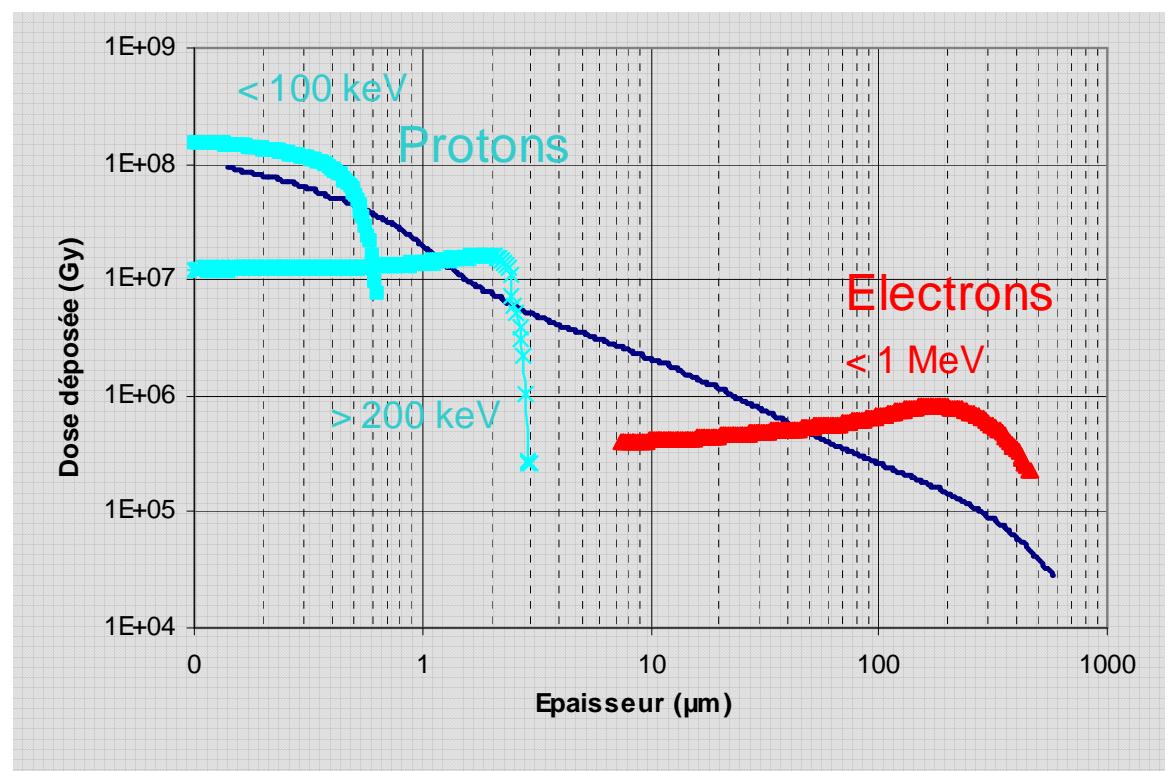
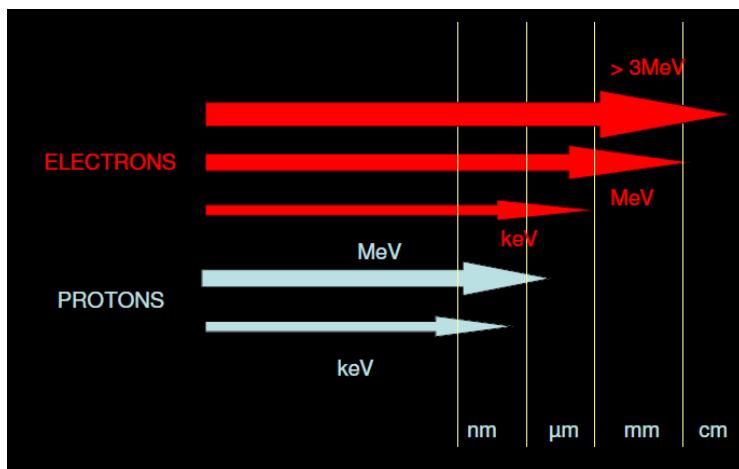
TOTAL DOSE IRRADIATION TEST PLAN DATA SHEET	
PART: UC1834	MANUFACTURER: UNITRODE
FUNCTION: REGULATOR	
SOURCE: Co 60	DOSE RATE: $\leq 360 \text{rad(s)} / \text{hour}$
STEPS: 0,10,20,30,50,70,100 (krad(s))	SPECIFICATION : ESA SCC 22900
ANNEALING: Under bias 24Hrs / 25° + 168 Hrs / 100°C	



PARAMETERS TO MEASURE PRE AND POST RADIATION :		
CHARACTERISTICS	SYMBOLS	TEST CONDITIONS
Standby Supply Current + 1,5 Volt reference :	Icc	
Output Voltage 1	Vout 1	
Line Regulation 1	Kvi1	Vin = 5 to 35V
Load Regulation 1	Kvo1	Iout = 0 to 2 mA
-2 Volt reference :		
Output Voltage 2	Vout2	
Line Regulation 2	Kvi2	Vin = 5 to 35 V
<u>Error Amplifier section :</u>		
Input Offset Voltage	Vos	Vcm = 1.5V
Input Offset Current	los	
Bias Current on + of Error Amplifier	IbiasE+	Vcm = 1.5V; vdm = 5 mV
Bias Current on - of Error Amplifier	IbiasE-	Vcm = 1.5V; vdm = 5 mV
<u>Current sense amplifier section :</u>		
Open Loop Gain		Output @Rn 14, Rn 12 = Vin+
Bias Current on + of Sense Amplifier	IbiasSh+	Vin = 15V
Bias Current on - of Sense Amplifier	IbiasSh-	Vin = 15V
Bias Current on + of Sense Amplifier	IbiasS1+	Vin = 0V
Bias Current on - of Sense Amplifier	IbiasS1-	Vin = 0V
<u>Threshold Voltage</u>		
0,5 V Threshold Voltage	Vth	Rn 4 open Vcm = Vin+ or Vin-
Adjustement Input Current	Iadj	Vin = 0,5V
<u>Driver section :</u>		
Driver Saturation Voltage	Vdsat	Iout = 100 mA
Maximum output current	Idout	
Driver Leakage Current	IDleak	Dvout = 30V
<u>Fault amplifier section :</u>		
Saturation Voltage	Vfsat	Iout = 1 mA
O.V. Latch Saturation Voltage	Vlsat	Iout = 1 mA
Crowbar Gate Current	Icgc	Vcg = 0V
Crowbar Gate Leakage Current	Idc	Vcg = 0V
OV Latch Output Current	Ilout	
Alert Output Current	Ifout	

- Test Definition -> DOSE PROFILE

- Necessity to combine different particles and energies to fit as good as possible the calculated dose (ECSS Q 70 06)
- A test covering one year in orbit for “volume effect” could represent less than one day for “surface effects”



Dose profile for kapton ($d=1.42\text{g.cm}^{-3}$) for 1year GEO and comparison with simulated dose profile

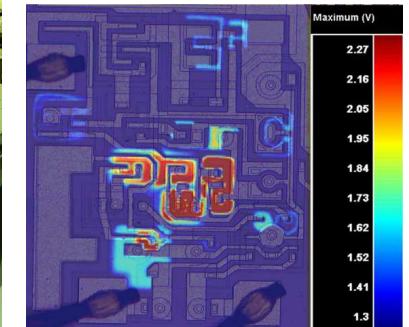
- Maintenance of test equipments
 - Regular controls by certified authority
- Adequation of test benches to application
 - Cable length (accuracy, signal/noise ratio)
 - Vacuum
 - pre-test using Cf source, laser
- Device preparation
 - Decapsulation / Identification of active zone
- Dosimetry of sources/accelerators & Radioprotection
 - TRAD has developed its own electronic dosimeters for Co60
 - TRAD has its own Co60 source with independent customer room
 - Entries controlled by alarms and operators follow-up / Security system

TEST FACILITIES



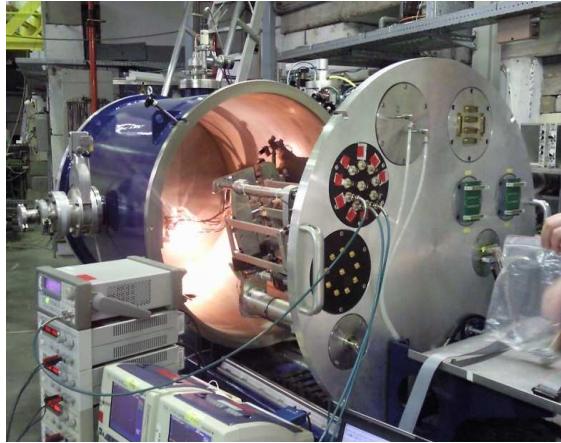
Cobalt 60 source

- Photonic dose
- 45m³ irradiation volume
- 7.4 TBq, beam dose rate from 10rad(Si)/h to 1krad(Si)/h, operating temperature at room temp



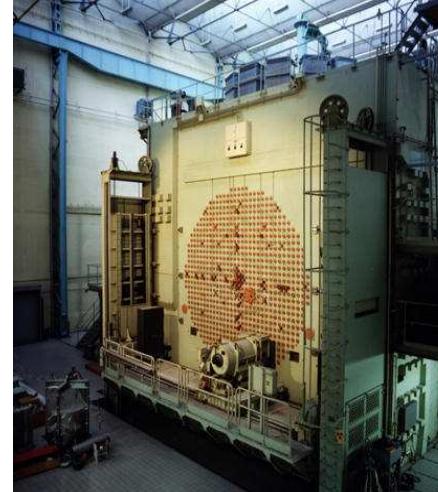
Laser

- SEE Simulation
- DUT cartography



Cyclotrons (HIF/RADEF)

- Ions HIGH LET value
- 67,7 MeV/mg/cm² up to 80 with 45° angle
- Ions High Range (92 µm)



Neutrons

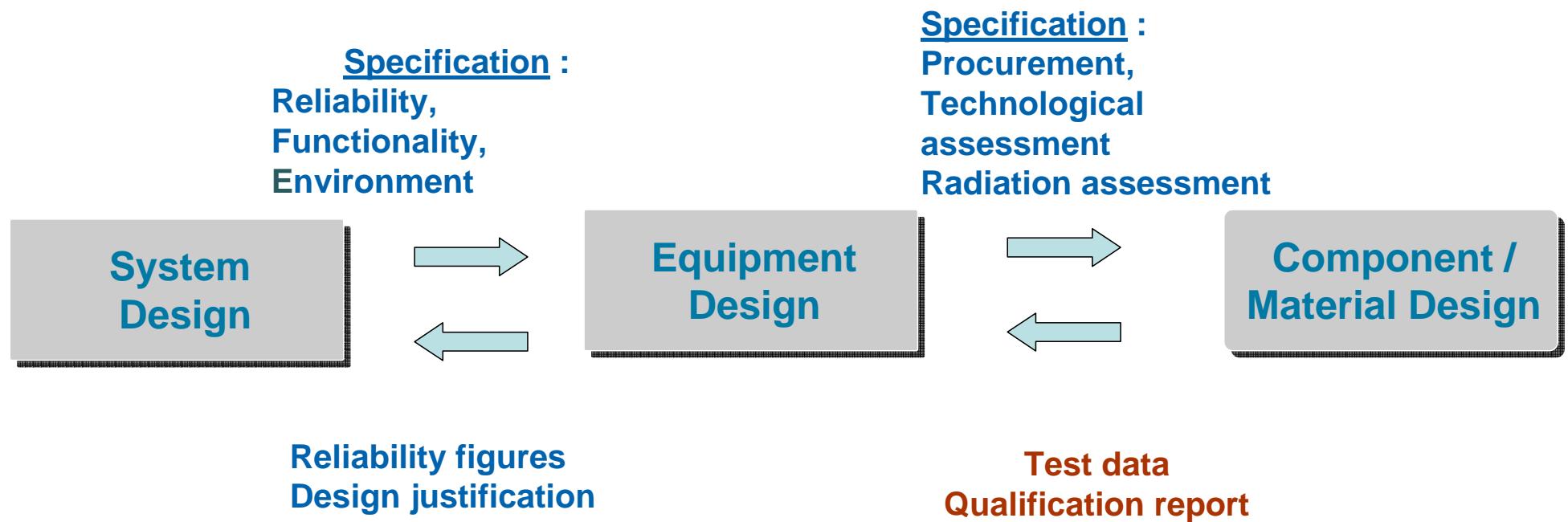
- High energy 1 MeV



Protons

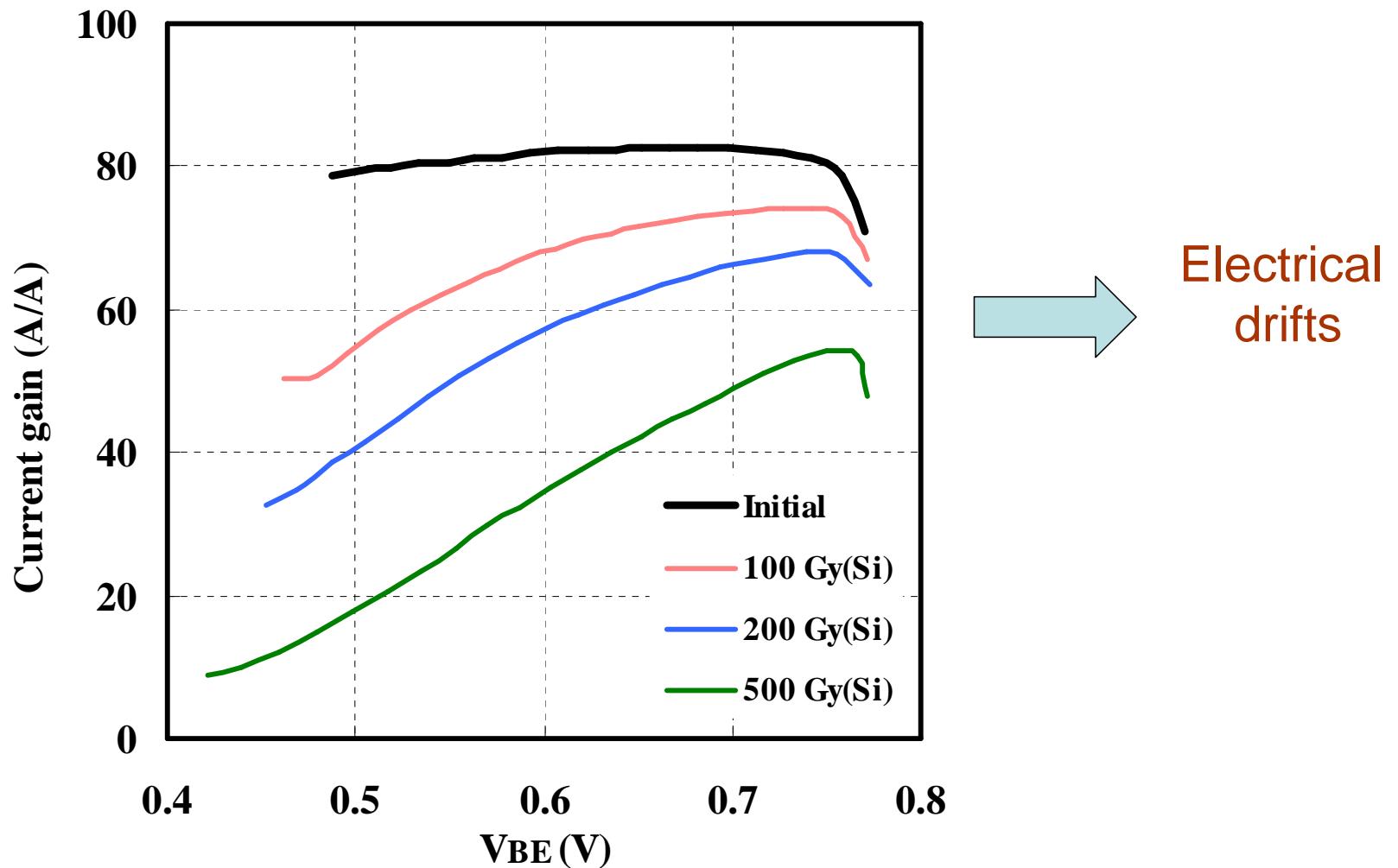
- Energy up to 200 MeV
- Flux : 2E8 p/cm²/s

• STEP 4 : Radiation Test Data Management

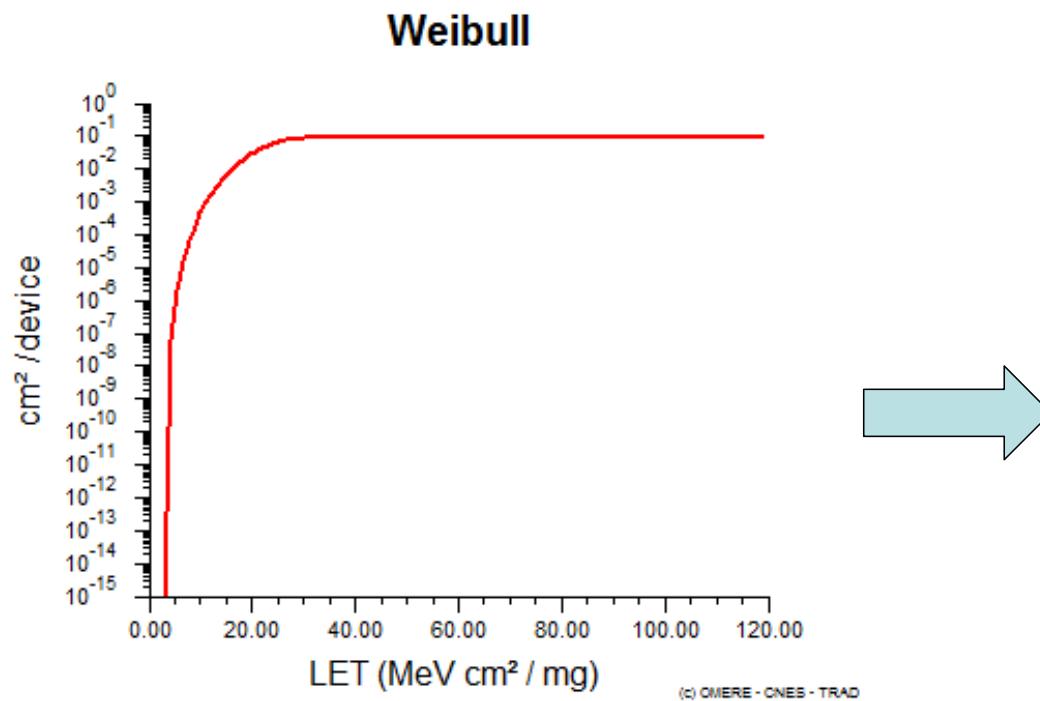


Supply Data to system engineer

- TID : Test report with impacted parameters

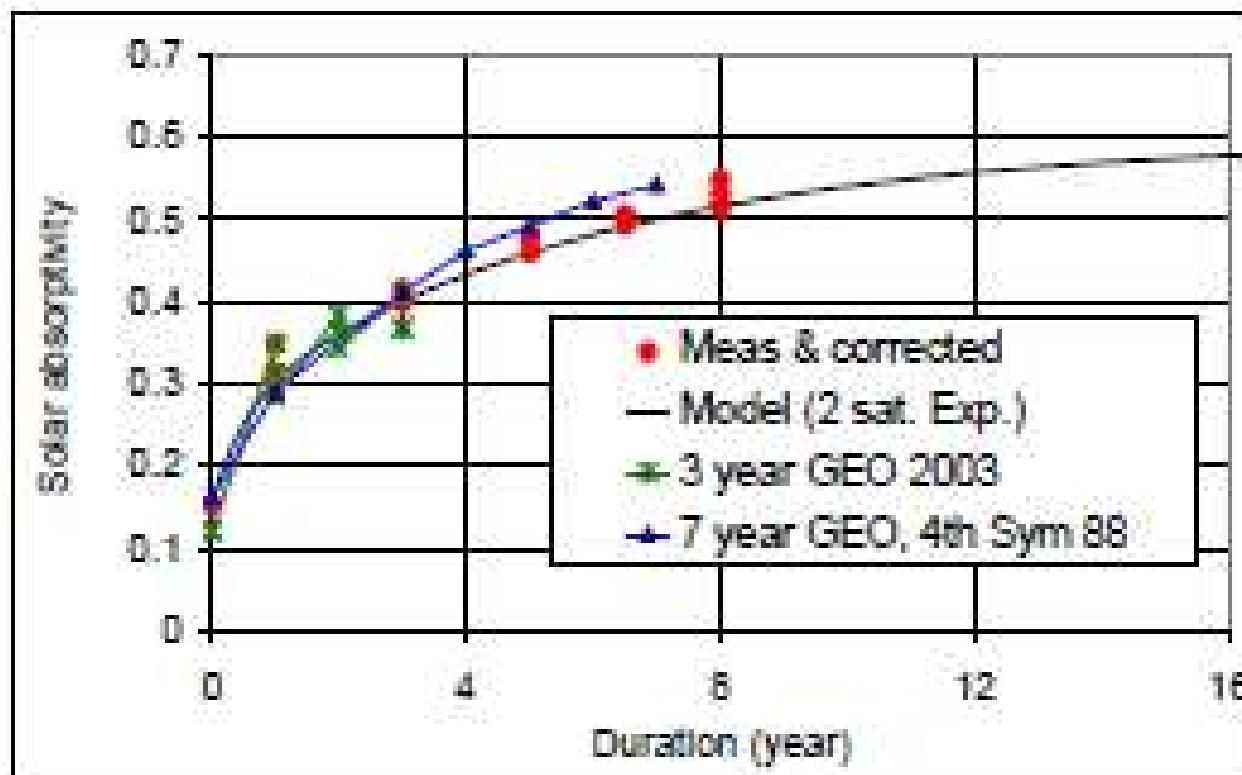


- SEE : Weibull fit of cross-section



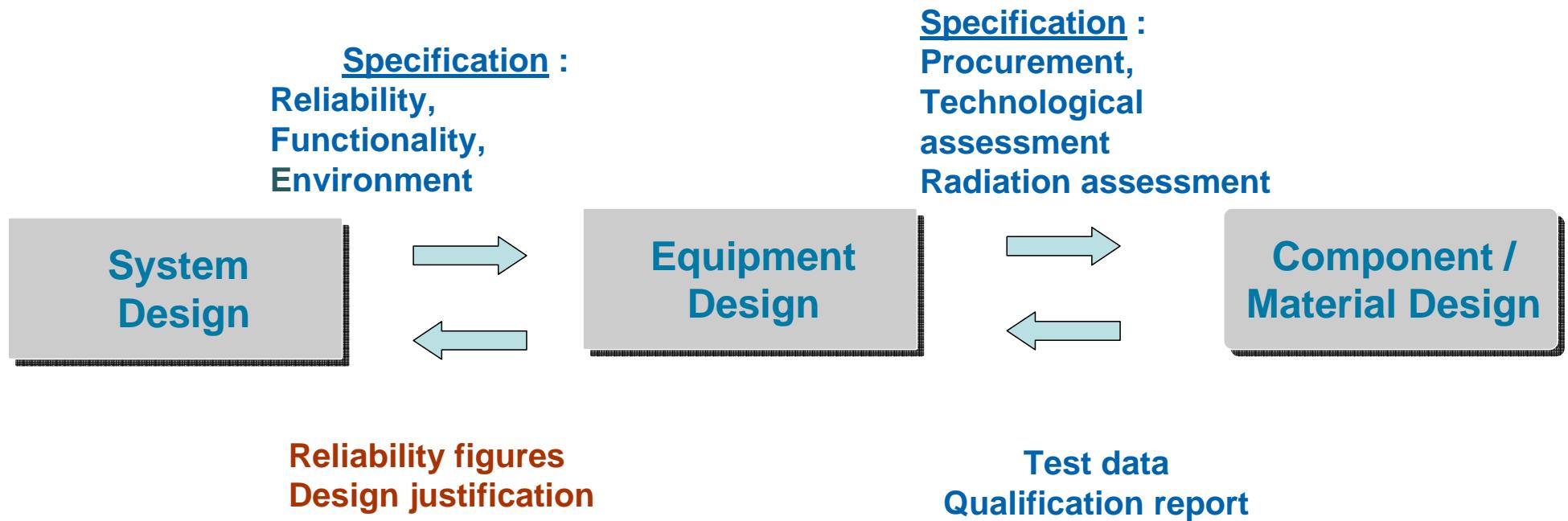
Single Event Rate
(#events /device/day)

- Change of solar absorptivity

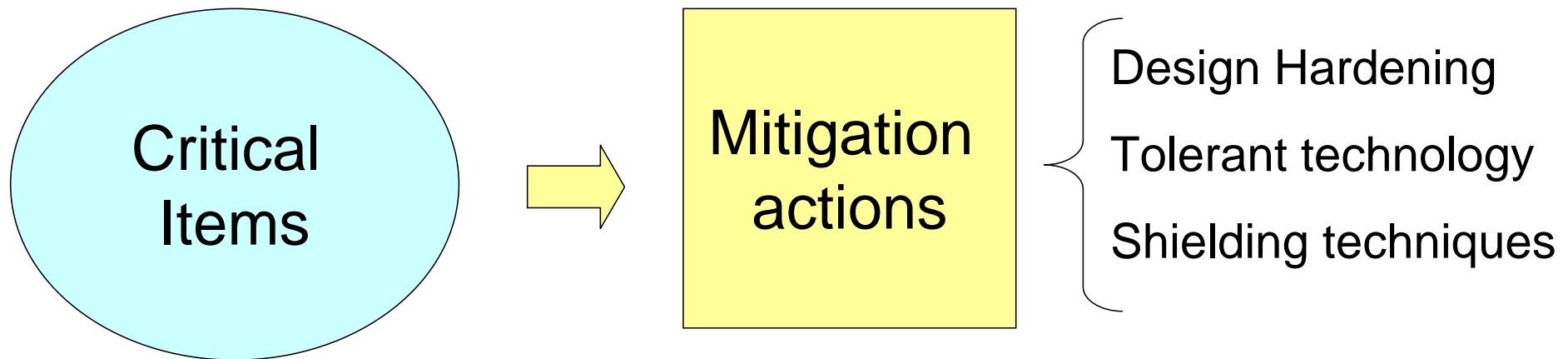


Thermal equilibrium
impact

- STEP 5 : Radiation Test Data Analysis



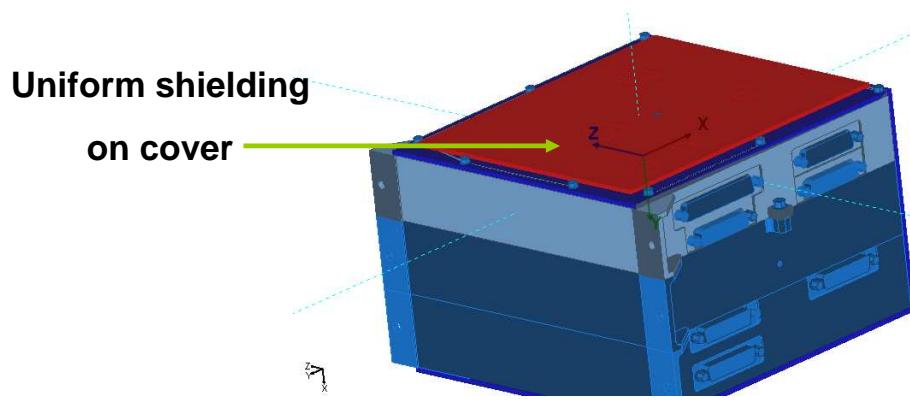
Radiation risks mitigation



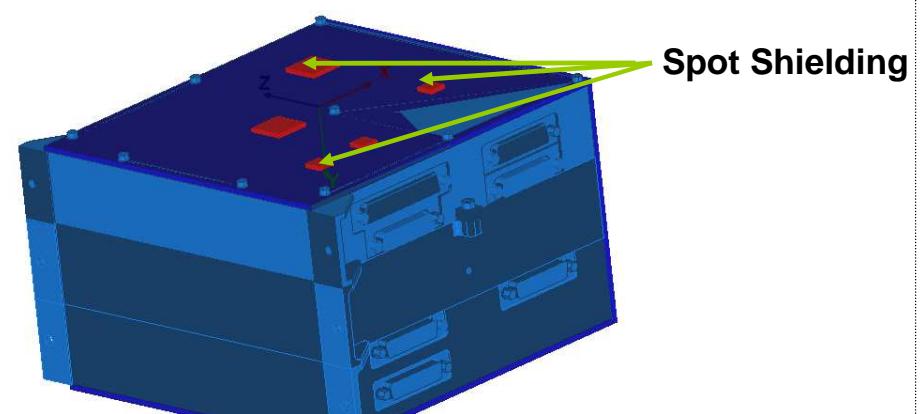
- Optimize shielding

Example : Shielding of one equipment for a geostationary mission

Without FASTRAD



With FASTRAD



Additional Shielding

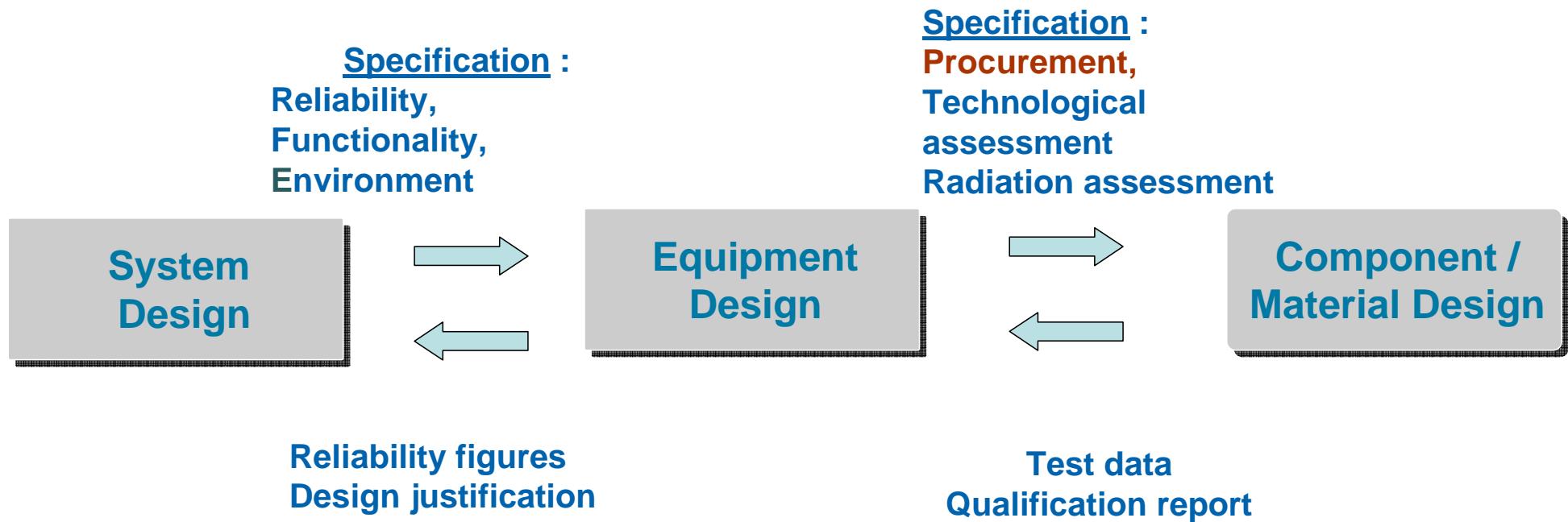
360 g

12 g

You save 350 g/equipment

- **Optimize design**
 - Adapt configurations (electronic, thermal)
 - Adapt derating rules (e.g. Power MOSFET) → ECSS Q 30 11
- **Reject some technologies.... And re-qualify good ones !**
 - Electronics :
 - SEE or SEL rate not acceptable
 - Unacceptable drifts
 - Materials :
 - Adhesive weakness
 - Radiation induced Optical absorption too high for glasses

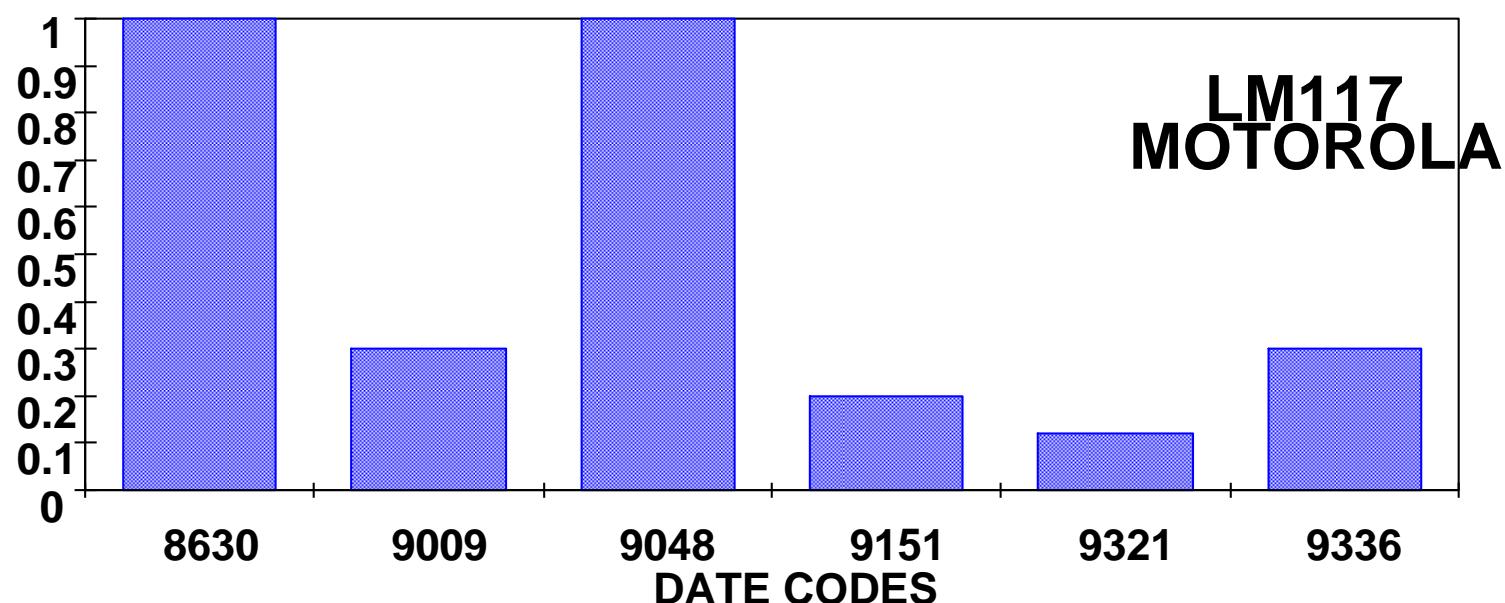
- STEP 6 : « Sustainable » Hardening



- Avoid sensitive technologies

- Updated Expert judgement
 - Critical Review of Declared Material and Declared Component Lists
 - Bibliographic studies (e.g RADECS, NSREC)
 - Field return based on background

- Test every flight lot of sensitive technologies (RVT)



« Emerging » topics

- **Laser / SEE**
 - Alternative to heavy ions ?
- **New technologies (MEMS, Opto, RF,...)**
 - New degradation mechanisms
 - New test techniques
 - Dose rate ?
- **« New » missions**
 - Interplanetary (Jupiter -> High Energy Electrons)
- **Sequenced / Synergetic effects (UV, Radiation, Thermal)**
 - JUICE, Solar missions

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